



#### **60V N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
60V	10mΩ @ V <sub>GS</sub> = 10V	128A

### **Description and Applications**

This new generation MOSFET has been designed to minimize the onstate resistance (RDS(on)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Controls
- **Engine Management Systems**
- **Body Control Electronics**
- **DC-DC Converters**

### **Features and Benefits**

- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- Low R<sub>DS(on)</sub> Minimizes Power Losses
- Low Qg Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

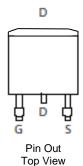
#### **Mechanical Data**

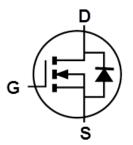
- Package: TO263AB
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 1.7 grams (Approximate)

TO263AB (D2PAK)



Top View





Internal Schematic

November 2021

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### **Ordering Information** (Note 4)

Part Number	Deskons	Packing		
Part Number	Package	Qty.	Carrier	
DMN6010SCTB-13	TO263AB (D2PAK)	800	Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

1 of 8 DMN6010SCTB Document number: DS43782 Rev. 2 - 2



### **Marking Information**



Ohle Manufacturer's Marking
N6010SCT = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 21 = 2021) WW = Week (01 to 53)

# **Maximum Ratings** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	60	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Durin Compant (Note C) \/ 40\/	T <sub>C</sub> = +25°C	ΙD	128	Α
Continuous Drain Current (Note 6) VGS = 10V	T <sub>C</sub> = +70°C		102	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	128	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	512	А	
Avalanche Current, L =0.1mH		las	71	А
Avalanche Energy, L = 0.1mH	Eas	252	mJ	

# Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	TA = +25°C	PD	5	W
Thermal Resistance, Junction to Ambient (Note 5)		RθJA	30	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	P <sub>D</sub>	312	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θ</sub> JC	0.4	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.6. Thermal resistance from junction to soldering point (on the exposed drain pad).



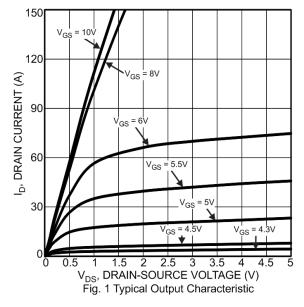
# Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	60	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	10	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	_	_	100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	2	_	4	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$	
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	_	7.7	10	mΩ	$V_{GS} = 10V, I_D = 25A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 25A$	
DYNAMIC CHARACTERISTICS (Note 8)						•	
Input Capacitance	Ciss	_	2692	_		V <sub>DS</sub> =25V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	_	909	_	pF		
Reverse Transfer Capacitance	Crss	_	65	_			
Gate Resistance	Rg	_	3.6	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	46	_		V <sub>DS</sub> = 44V, I <sub>D</sub> = 25A, V <sub>GS</sub> = 10V	
Gate-Source Charge	Qgs	_	12	_	nC		
Gate-Drain Charge	Qgd	_	13	_			
Turn-On Delay Time	t <sub>D(on)</sub>	_	13.5	_		$V_{DS} = 30V, V_{GEN} = 10V,$ $R_{L} = 1.2\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	44	_	1		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	45	_	ns		
Turn-Off Fall Time	tF	_	29	_			
Reverse Recovery Time	trr	_	51.5	_	ns	I <sub>F</sub> = 20A, di/dt = 100A/μs,	
Reverse Recovery Charge	Q <sub>RR</sub>	_	92	_	nC V <sub>R</sub> = 30V		

Notes:

<sup>7.</sup> Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.





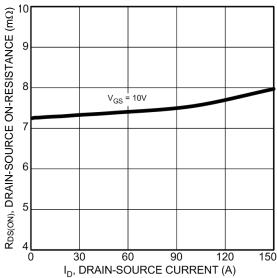


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

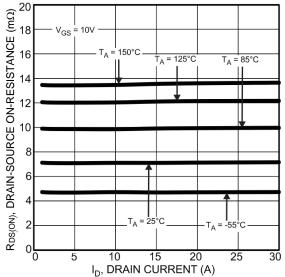
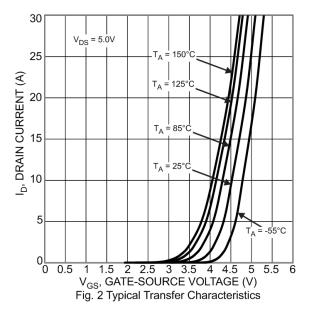
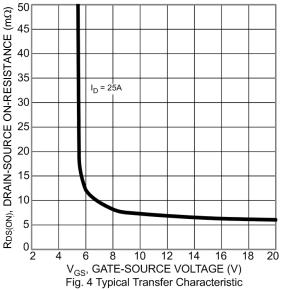
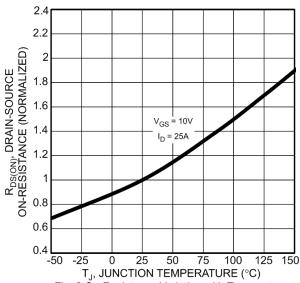


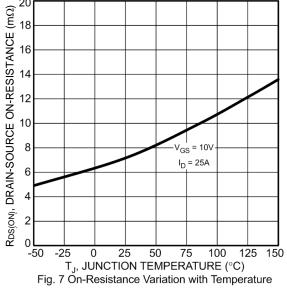
Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

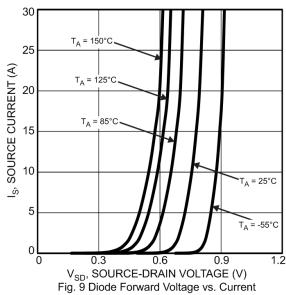


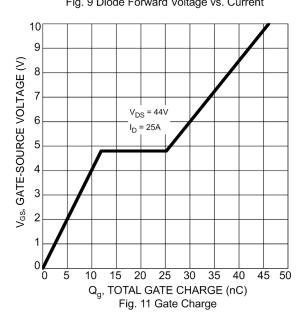












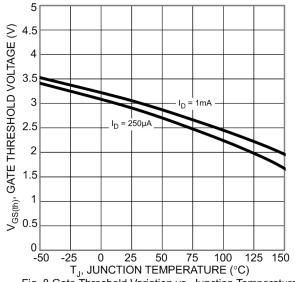
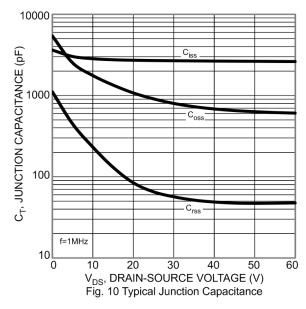
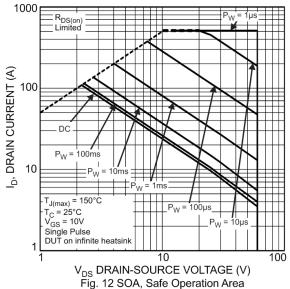
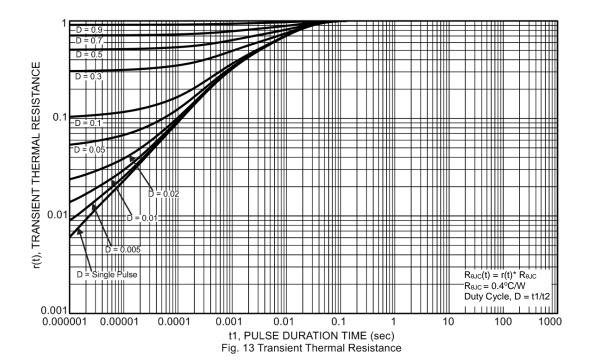


Fig. 8 Gate Threshold Variation vs. Junction Temperature







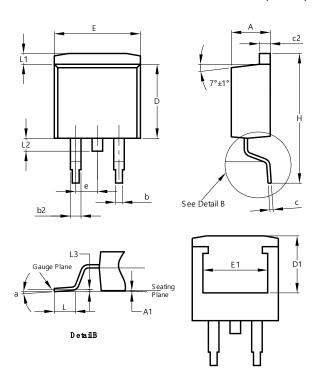




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TO263AB (D2PAK)

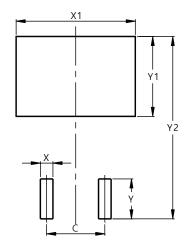


TO263AB (D2PAK)				
Dim	Min	Max	Тур	
Α	4.07	4.82	-	
A1	0.00	0.25	-	
b	0.51	0.99	-	
b2	1.15	1.77	-	
С	0.356	0.73	-	
c2	1.143	1.65	-	
D	8.39	9.65	-	
D1	6.55	6.95	-	
е		2.54 T\	/P	
Е	9.66	10.66	-	
E1	6.23	8.23	-	
Н	14.61	15.87	-	
L	1.78	2.79	-	
L1	-	1.67	-	
L2	-	1.77	-	
L3	-	-	0.254	
а	0°	8°	-	
All Dimensions in mm				

# **Suggested Pad Layout**

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

### TO263AB (D2PAK)



Dimensions	Value (in mm)		
C	5.08		
Х	1.10		
X1	10.41		
Y	3.50		
Y1	7.01		
Y2	15.99		



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